

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (MMBT5551)
- Ideal for Low Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 2 and 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Top View

Device Schematic

В

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	lc	-600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
	Gymbol		
Power Dissipation (Note 1)	PD	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ ext{ heta}JA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	Do

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

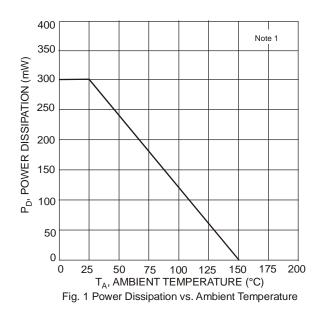
 2. No purposefully added lead. Halogen and Antimony Free.
3. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

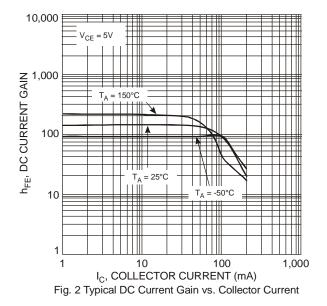


Electrical Characteristics @T_A = 25°C unless otherwise specified

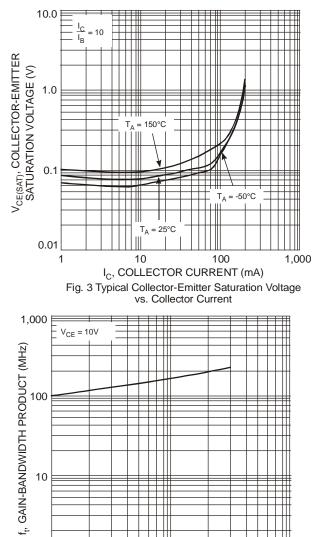
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160	_	V	$I_{C} = -100 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150		V	$I_{\rm C} = -1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_{E} = -10 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CBO}	_	-50	nA μA	$V_{CB} = -120V, I_E = 0$ $V_{CB} = -120V, I_E = 0, T_A = 100^{\circ}C$
Emitter Cutoff Current	I _{EBO}		-50	nA	$V_{EB} = -3.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	50 60 50	 240 	_	I _C = -1.0mA, V _{CE} = -5.0V I _C = -10mA, V _{CE} = -5.0V I _C = -50mA, V _{CE} = -5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.2 -0.5	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$ $I_{C} = -50mA$, $I_{B} = -5.0mA$
Base-Emitter Saturation Voltage		_	-1.0	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$ $I_{C} = -50mA$, $I_{B} = -5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}		6.0	pF	$V_{CB} = -10V$, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	40	200		$V_{CE} = -10V, I_C = -1.0mA,$ f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = -10V, I _C = -10mA, f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5.0V, I_C = -200\mu A,$ $R_S = 10\Omega, f = 1.0kHz$

Notes: 4. Short duration pulse test used to minimize self-heating effect.









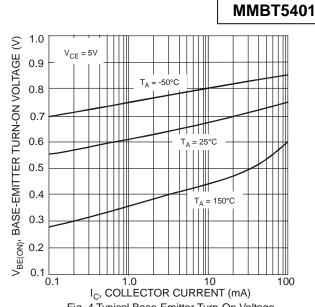


Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

Ordering Information (Note 5)

10 I_C, COLLECTOR CURRENT (mA)

Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current

Part Number	Case	Packaging
MMBT5401-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

1

1

K4M	ΥM	K4M = P YM = Da Y = Year
		M = Mon

100

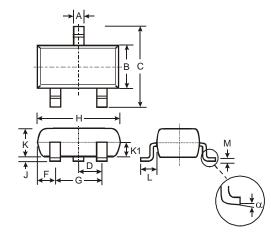
K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002)

M = Month (ex: 9 = September)

Date Code	e Key						-											
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	М	Ν	Р	R	s	Т	U	V	W	Х	Y	Z	Α	В	С
Month	Jan	۱	Feb	Ма		Apr	May	/	Jun	Ju		Aug	Sep		Oct	Nov	,	Dec
Code	1		2	3		4	5		6	7		8	9		0	N		D

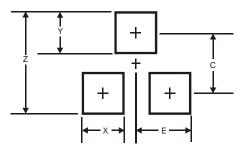


Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
κ	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	Dimens	ions in	mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.